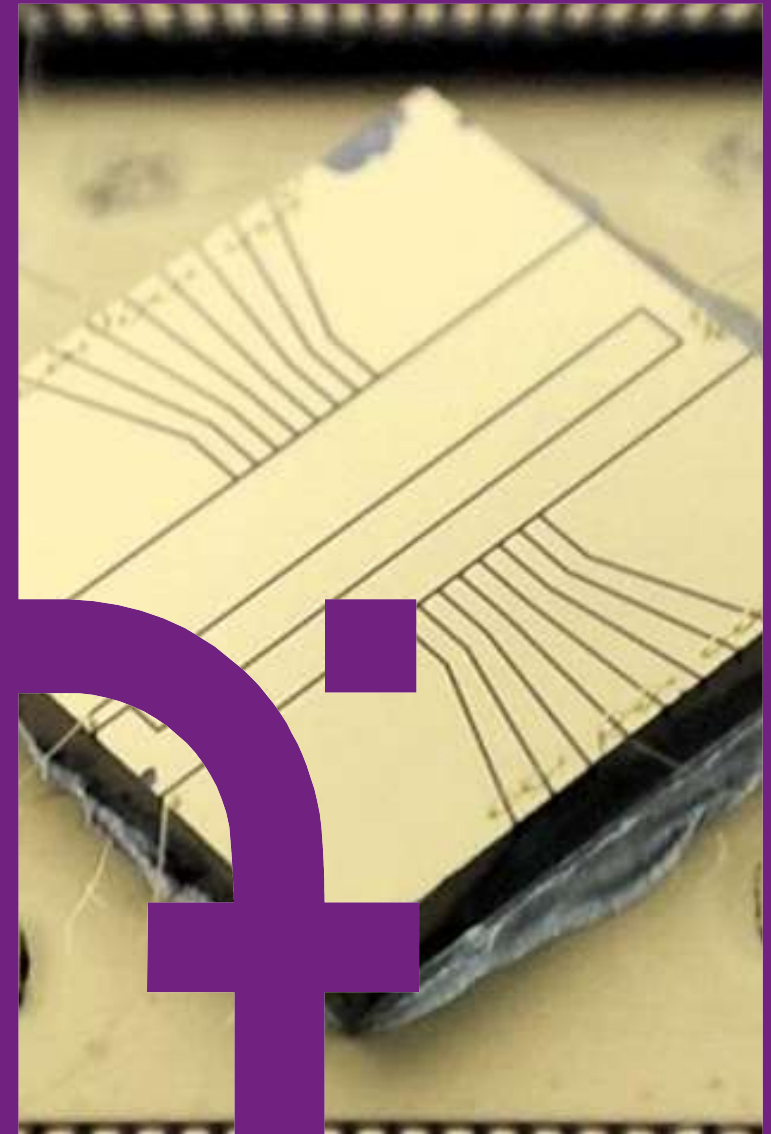


COMPACT YB⁺ CLOCK

Alan Boudrias, Valérie Soumann, Moustafa Abdel-Hafiz, Clément Lacroûte – 8 octobre 2025



SINGLE-ION YB⁺ OPTICAL CLOCK

Optical clocks reach fractional frequency stabilities of $\sim 10^{-15} \tau^{-1/2}$ for single-ion clocks to $< 10^{-16} \tau^{-1/2}$ for optical lattice clocks, and fractional **accuracies of 10^{-18}** and below [1].

- BIPM has defined a roadmap for the redefinition of the SI second;
- several proposals consider a multi-species definition;
- relativistic effects have been tested with 18-digits precision, and **height measurements** reach the cm level [2].

⇒ Several calls and projects aim at the implementation of continental **optical clocks network** [3,4].

⇒ Future optical timescales will require flywheel oscillators, equivalent to H-Masers.

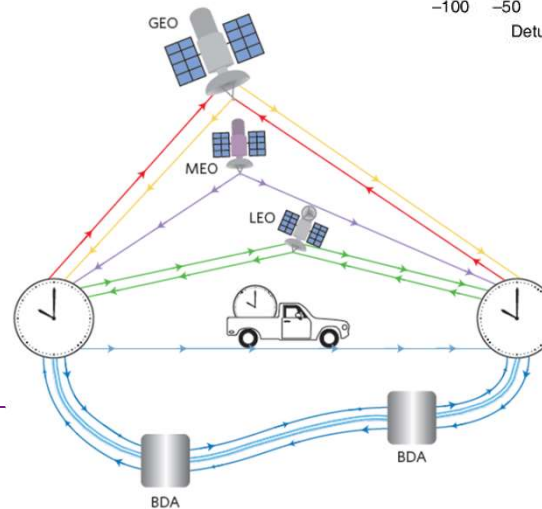
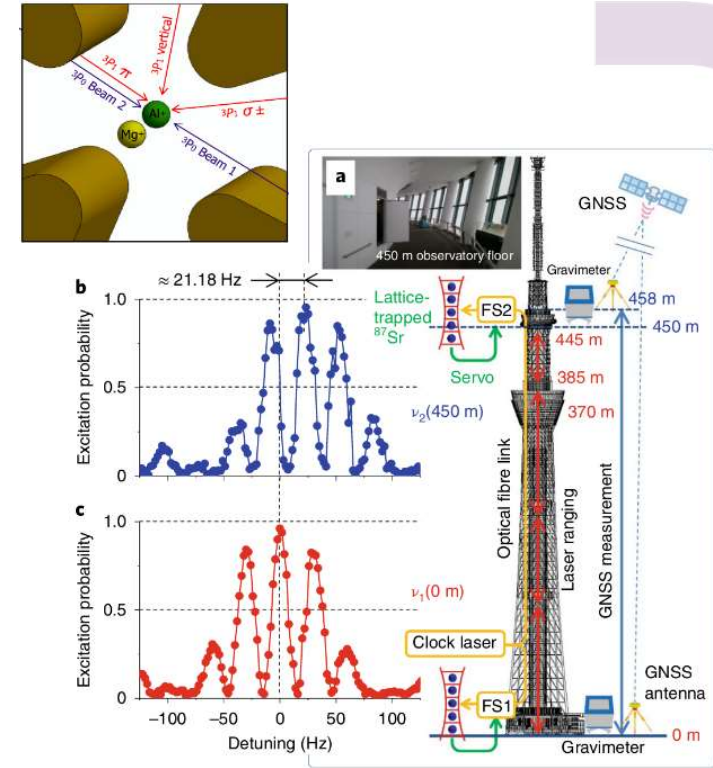
⇒ Robust, continuous-operation clocks must be built.

[1] Brewer *et al.*, PRL 123, 033201 (2019)

[2] Takamoto *et al.*, Nat. Phot. 14, 411-415 (2020)

[3] C. Lisdat *et al.*, Nat. Comm. 7, 12443 (2016)

[4] F. Riehle, Nat. Phot. 11, 25 (2017)



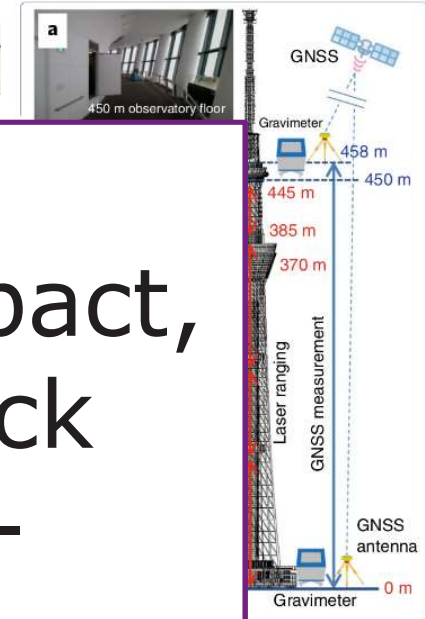
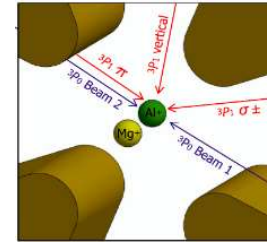
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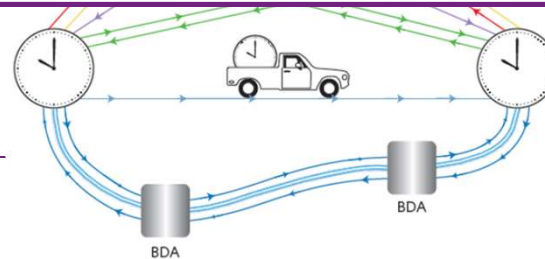
- BIPM has defined a roadmap for the redefinition of the SI second;
- several proposals of optical clocks;
- relativistic effects on time, frequency, precision, and height [2].

- ⇒ Several calls and initiatives for a continental **optical clock**
- ⇒ Future optical time scale equivalent to H-Ma
- ⇒ Robust, continuous

- [1] Brewer *et al.*, PRL 123, 033201 (2019)
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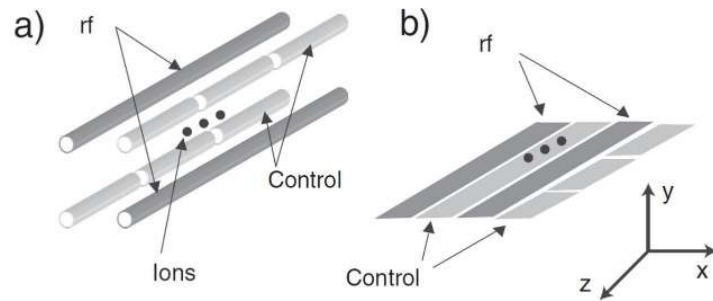


We are building a compact, single-ion optical clock based on a surface-electrode trap



SURFACE-ELECTRODES ION TRAPS

Optical single-ion clocks are usually based on 3D electrodes geometries (linear Paul traps, ring traps, endcap traps...), either machined or micro-fabricated.

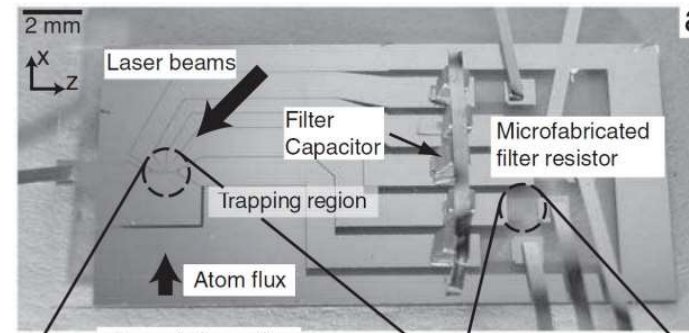
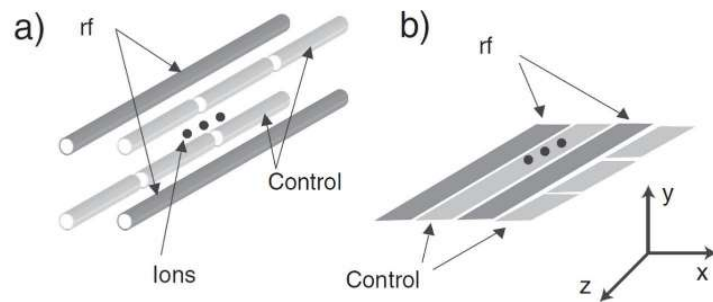


From Seidelin *et al.*, PRL 96, 253003 (2006).

SURFACE-ELECTRODES ION TRAPS

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Since their demonstration in 2006, Surface-electrode geometries have been widely used within the QIP community, allowing the fast and coherent control of single-ions and the integration of additional functions to the trap (integrated beam couplers, detection, microwave lines...)

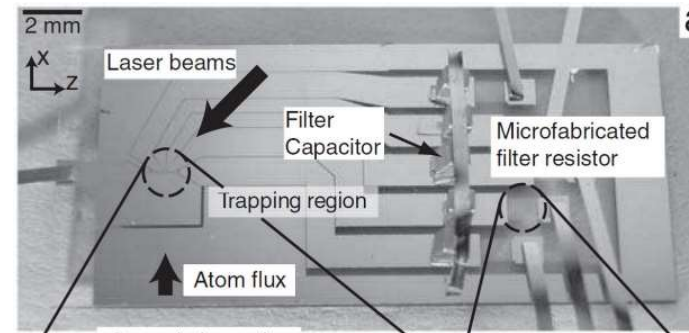
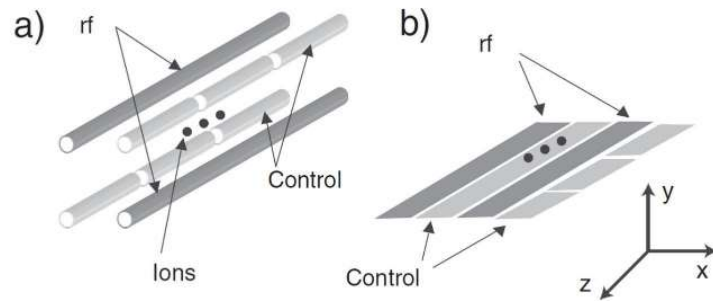


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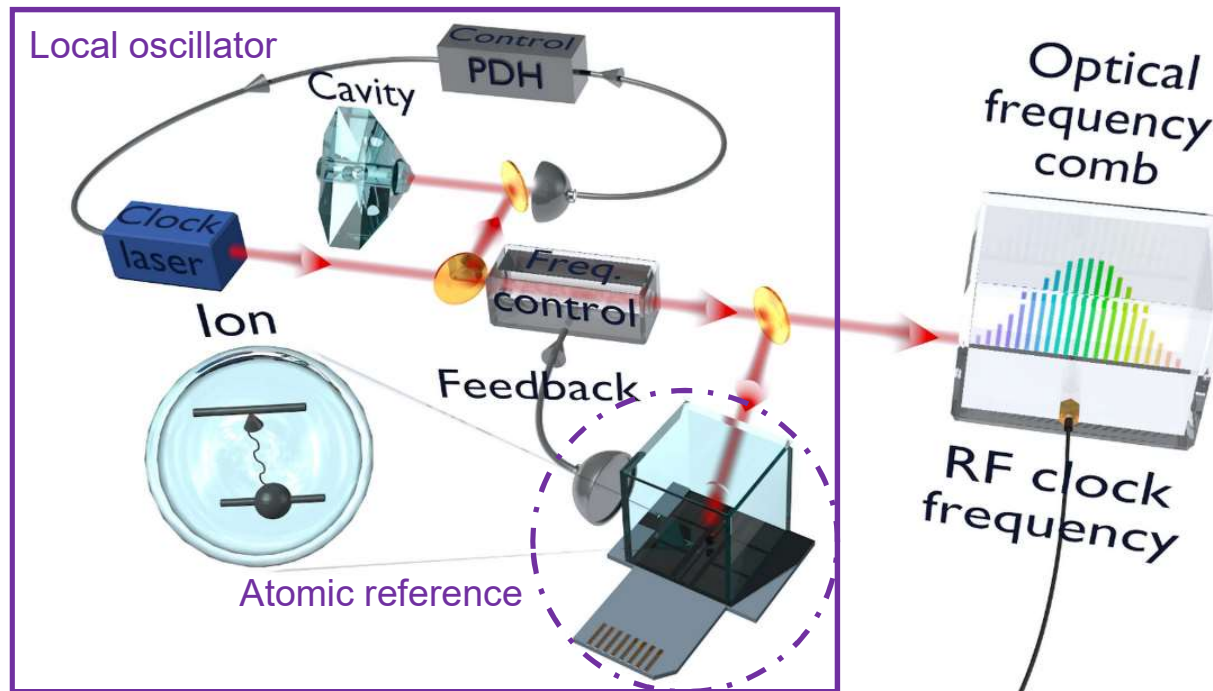
From Seidelin *et al.*, PRL 96, 253003 (2006).

- Simple geometries;
 - versatility;
 - easy fabrication with trad. clean-room processes;
 - good control of surface quality and tolerances.
- Anomalous heating;
 - low breakdown voltages;
 - shallower traps;
 - shorter lifetimes.

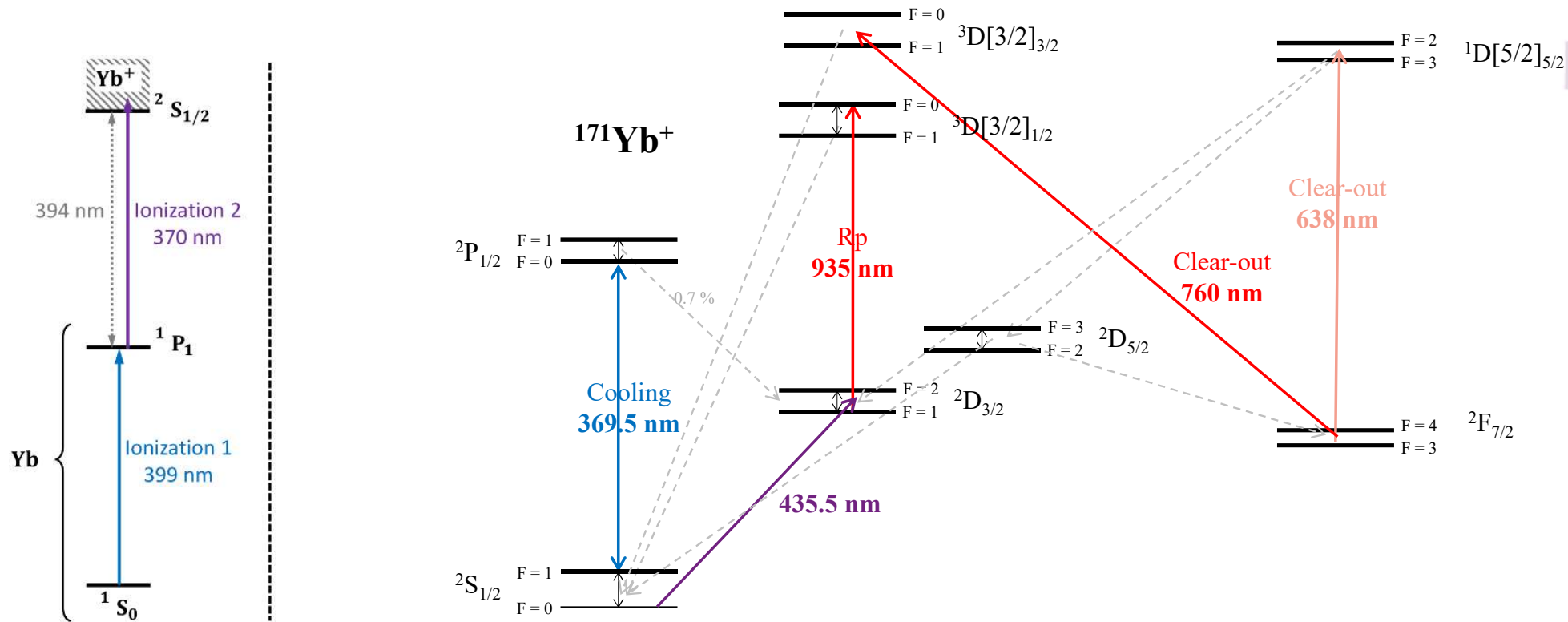
OBJECTIVES

We are building a compact optical clock based on a surface-electrode trap for $^{171}\text{Yb}^+$, with target volume and fractional frequency stability of $<500 \text{ L}$ and $10^{-14} \tau^{-1/2}$.

We are working on the E2 transition at 435.5 nm.



YB⁺ STRUCTURE



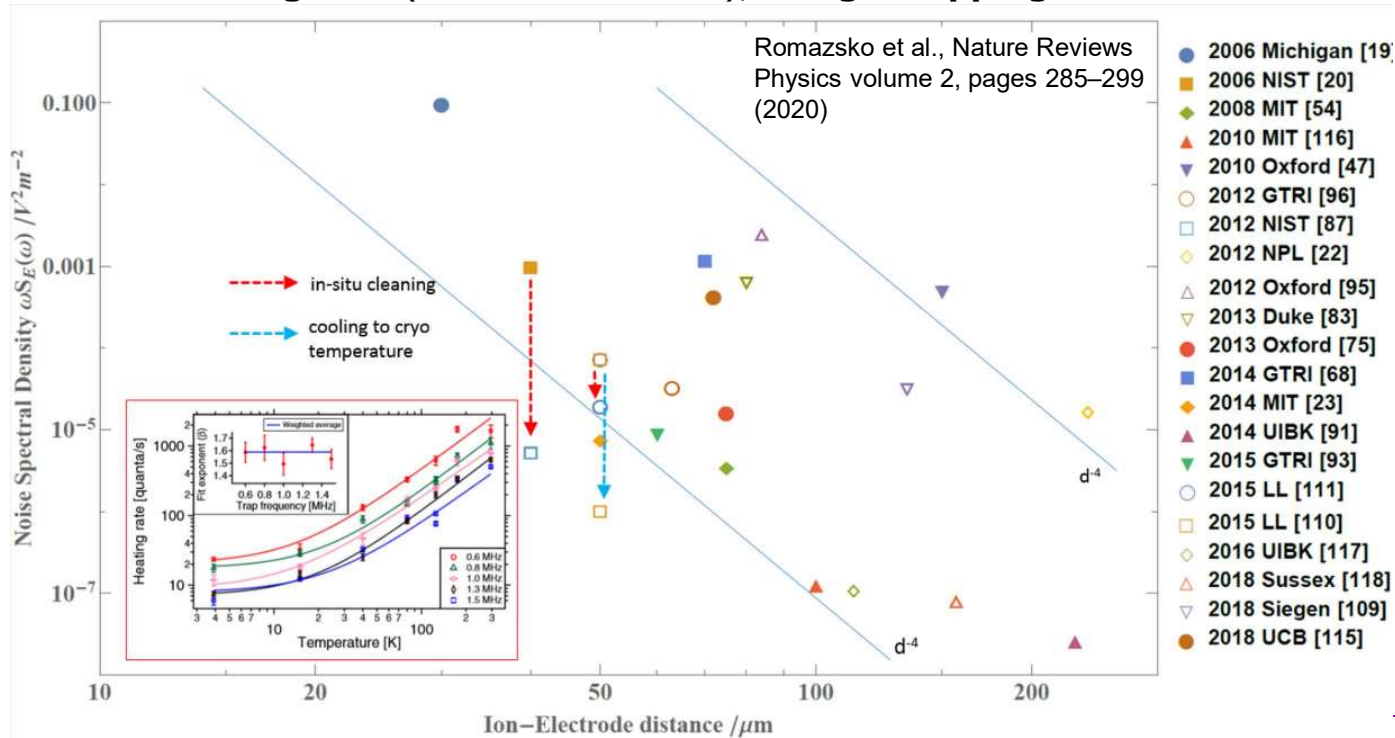
SURFACE-ELECTRODES ION CLOCK

- Operate in the **Lamb-Dicke regime** (Doppler effect rejection), *ie* high trapping frequencies.
- **Low micromotion** (2^d order Doppler effect rejection).
- **Long lifetime** (avoid deadtimes linked to ion loading).
- **Low heating rate** (avoid decoherence), *ie* high trapping distance.

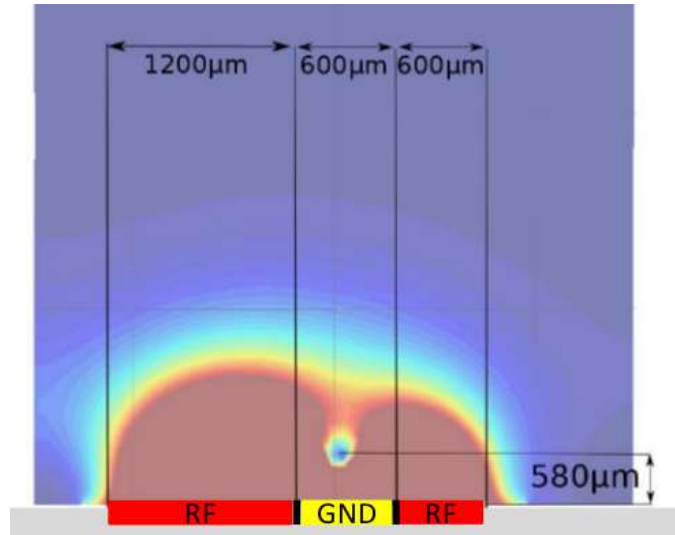
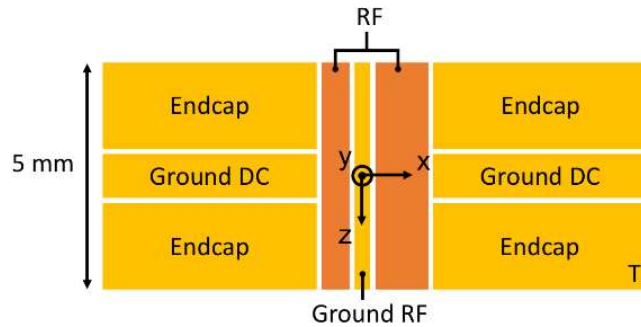


SURFACE-ELECTRODES ION CLOCK

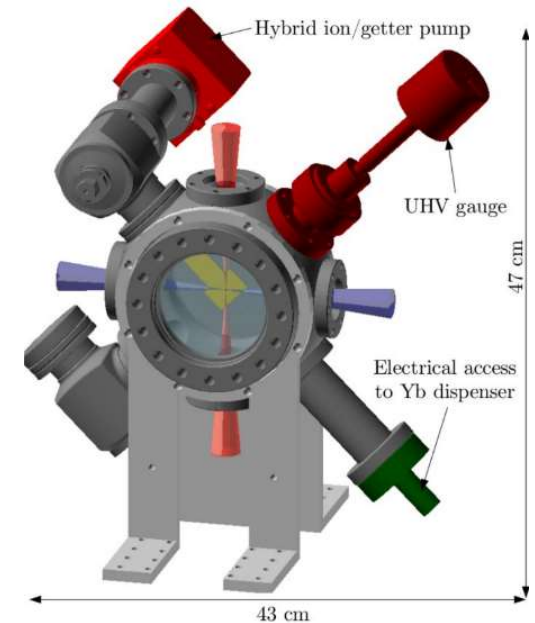
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TRAP DESIGN – 5-WIRE GEOMETRY



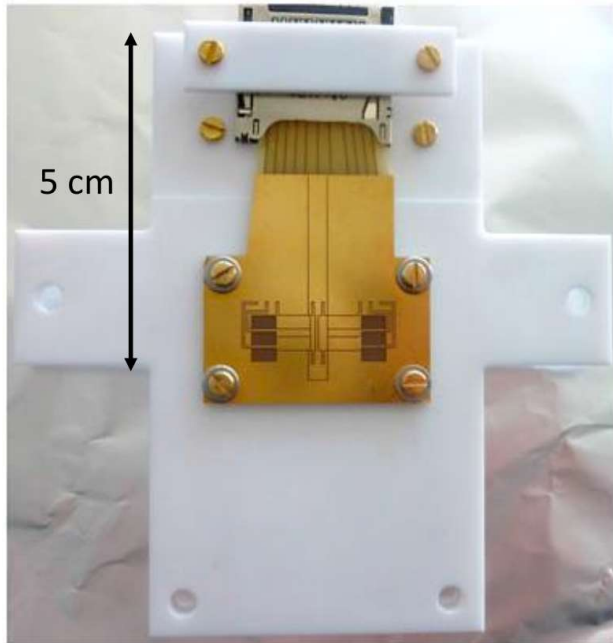
- RF electrodes widths: 600 μm and 1200 μm
- Trapping distance: $\sim 500 \mu\text{m}$
- $\Omega_{\text{RF}}/(2\pi) \sim 3 \text{ to } 6 \text{ MHz}$, $V_{\text{RF}} = 75\text{-}150 \text{ V}$
 $\omega_{\text{ax}}/(2\pi) \sim 85 \text{ kHz}$
 $\omega_{\text{rad}}/(2\pi) \sim 350 \text{ kHz}$



PROTOTYPE TRAP

Prototype chip trap:

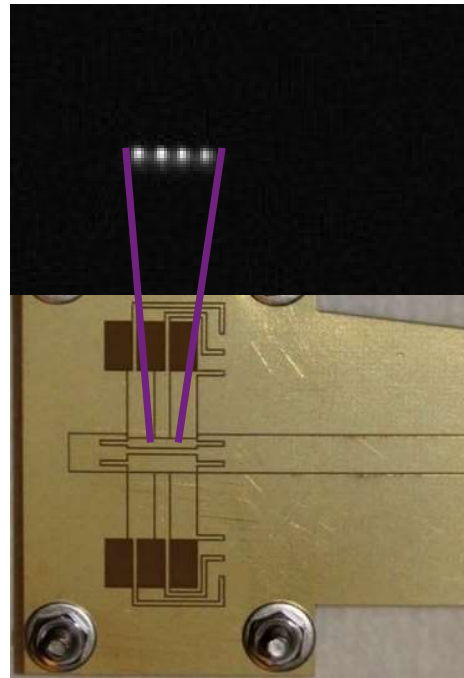
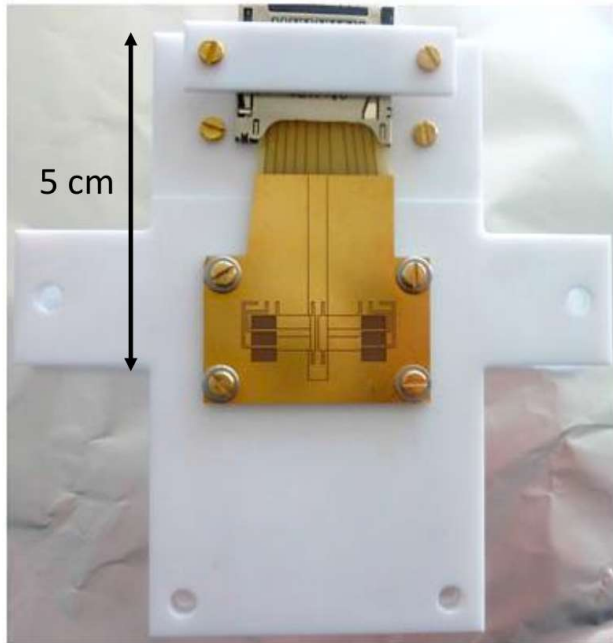
- 9 gold-plated copper electrodes on FR4 PCB
(not high-vacuum graded)
- RF electrodes widths: 600 μm and 1200 μm
- Trapping distance: $\sim 500 \mu\text{m}$
- $\Omega_{\text{RF}}/(2\pi) \sim 5.7 \text{ MHz}$, $V_{\text{RF}} = 150 \text{ V}$
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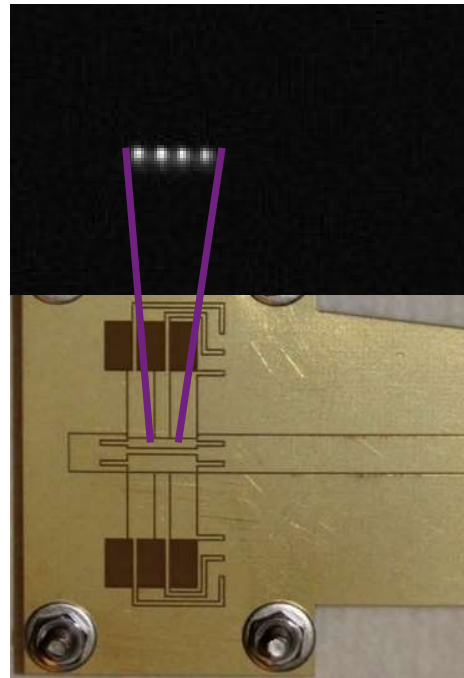
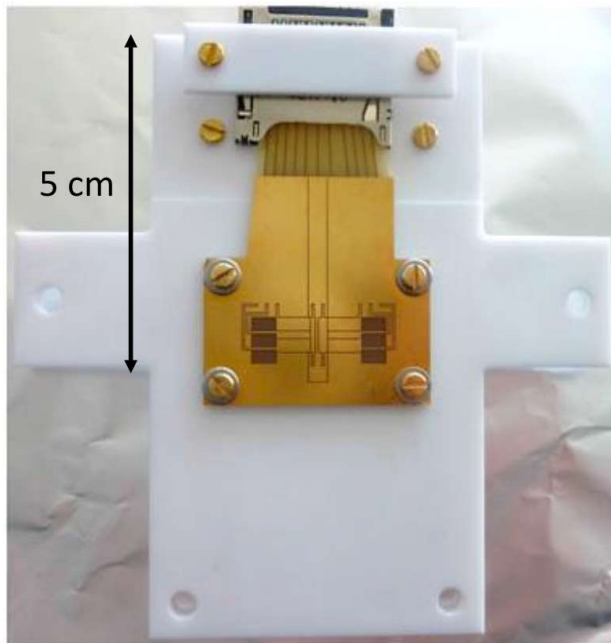
Starting with $^{176}\text{Yb}^+$ for simplicity

- $\Rightarrow$ Fluorescence detection using a high NA optics, a CCD camera for spatial resolution (magnification $\sim \times 6$) and/or a PMT for detection efficiency (collection efficiency 2.1%) and good SNR
- $\Rightarrow$ Detection axis = perpendicular to the chip

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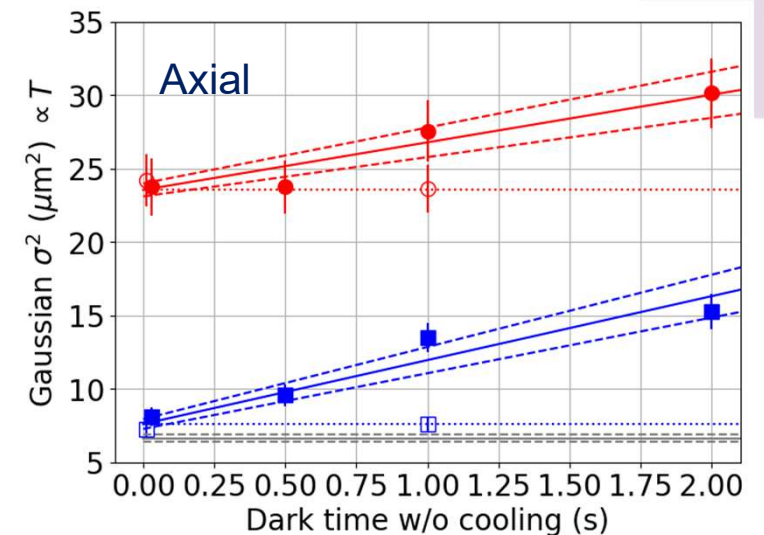
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Trap lifetime $\sim 1500 \text{ s}$

Trapping frequencies from 250 to 350 kHz

Heating rate $\sim 8000 \text{ phonons/s}$



arXiv:2206.08215 / App. Phys. B 129, 37 (2023)

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PROTOTYPE CHIP – EXPECTED PERFORMANCES

Heating rate

$8 \cdot 10^3$ phonons/s

Trapping frequencies 350 kHz



Clock operation:

Reduction of probing duration to a **few ms only** (vs $\tau_{D3/2} \sim 53$ ms)

$$\Rightarrow \sigma_y \sim 5 \cdot 10^{-14} \tau^{-1/2}$$

Micromotion

Compensated using AM modulation of the RF voltage

Stark: calculation from exp.

measurements;

Quadrupole: estimated from literature.

Shift	Prototype trap	Prototype trap advanced	State-of-the-art materials
2 ^d order Doppler	3.1×10^{-17}	3.1×10^{-17}	$\approx 10^{-18}$ [50]
Stark	3.6×10^{-17}	1.2×10^{-17}	$\approx 10^{-18}$ [51]
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PROTOTYPE CHIP – EXPECTED PERFORMANCES

Heating rate

$8 \cdot 10^3$ phonons/s

Trapping frequencies 350 kHz

Micromotion

Compensated using AM modulation
of the RF voltage

Short lifetime

Heating rate

Should be improved

Micromotion

⇒ use photo-correlation at trap secular
frequencies to implement 3D
optimization with a single beam

Lifetime

Use UHV-compatible materials for the chip

Shift	Prototype trap	Prototype trap advanced	State-of-the-art materials
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MICRO-FABRICATED TRAP

New chip

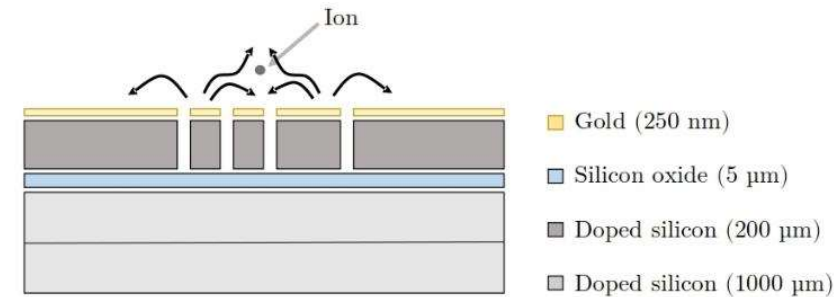
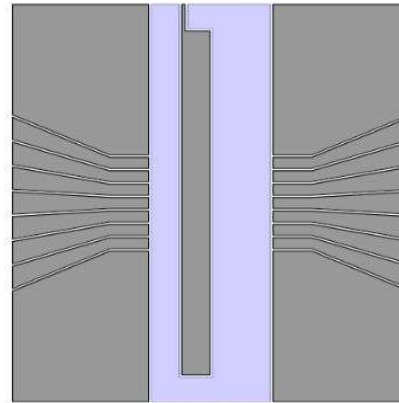
- ✓ Designed and produced locally in clean room
 - SOI electrodes
 - Gold plated
 - Much smaller dielectric interspacings
 - Cleaned by plasma

Trapping parameters

- Trapping frequencies of 250 kHz or more
 - Increase V_{RF}
 - Lower Ω_{RF}

Better materials

- ⇒ better vacuum
- ⇒ lower heating rate



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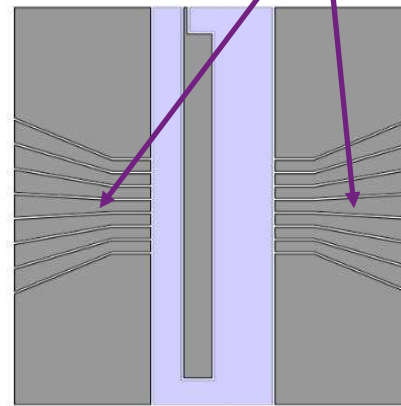
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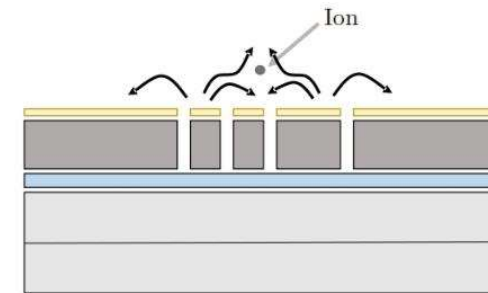
- ⇒ better vacuum
- ⇒ lower heating rate

Additional control electrodes
⇒ EMM compensation
⇒ Possible to use multiple trapping locations



Center electrodes width identical to prototype

Inter-electrodes spacing = 20 μm

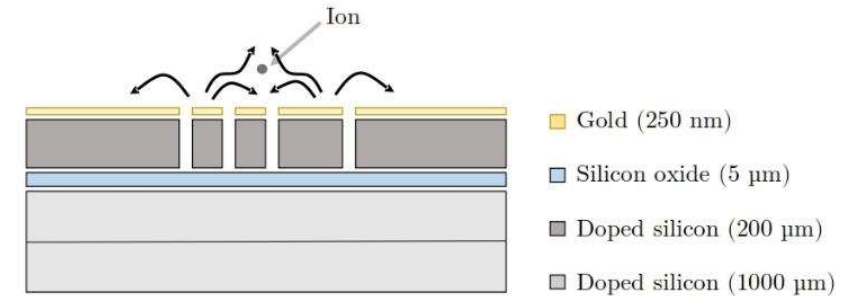
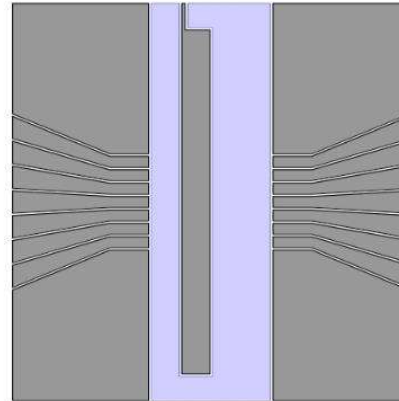


- Gold (250 nm)
- Silicon oxide (5 μm)
- Doped silicon (200 μm)
- Doped silicon (1000 μm)

MICRO-FABRICATED TRAP

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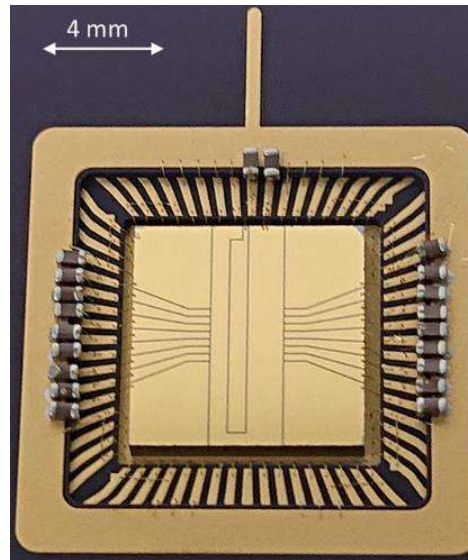


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Commercial ceramic chip-carrier

Filtering capacitors on all DC electrodes

MICRO-FABRICATED TRAP

New chip

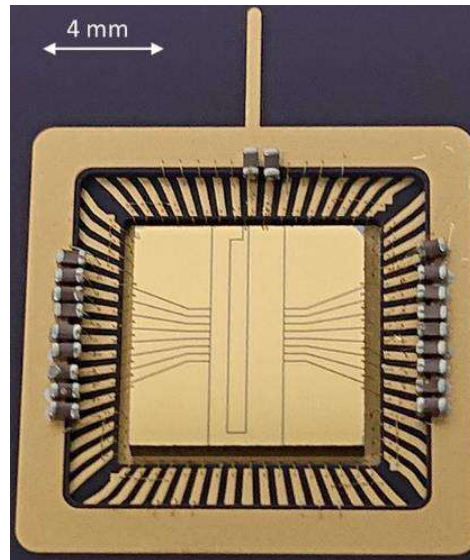
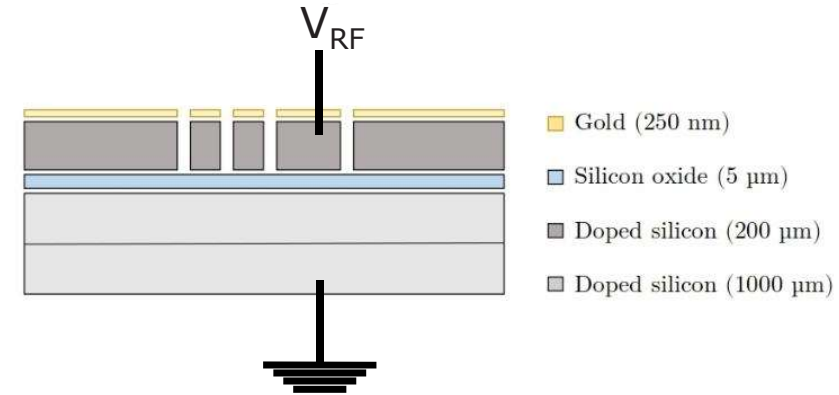
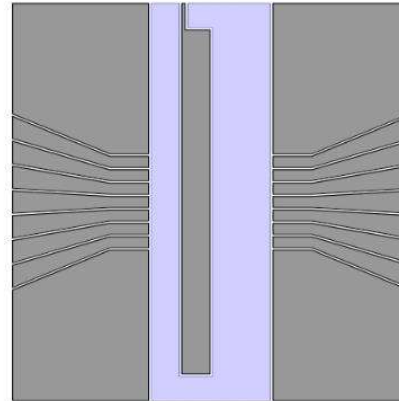
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Initial goal: 500 Vpp
(or more!)

MICRO-FABRICATED TRAP: BREAKDOWN TESTS

Dedicated chamber

- UHV
- RF supply
- Optical access

Detect breakdown through

- Imaging
- Voltage monitoring
- Pressure monitoring

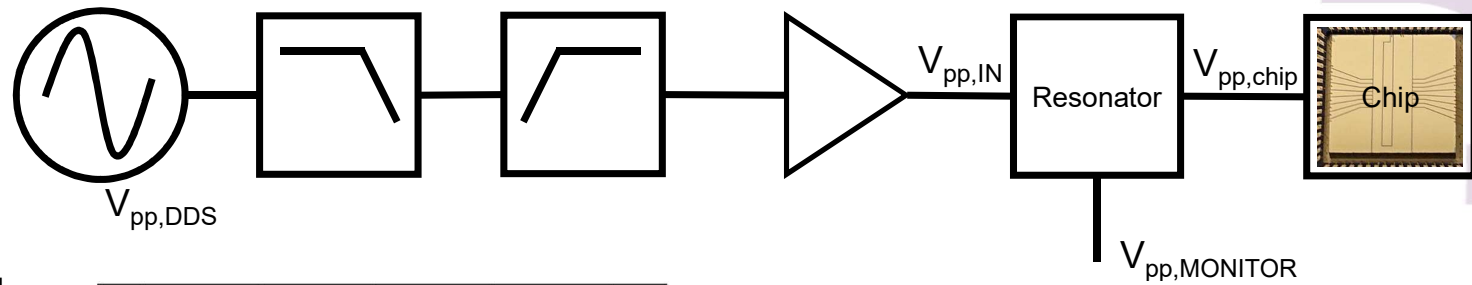
⇒ Very random results...



MICRO-FABRICATED TRAP: BREAKDOWN TESTS

Dedicated chamber

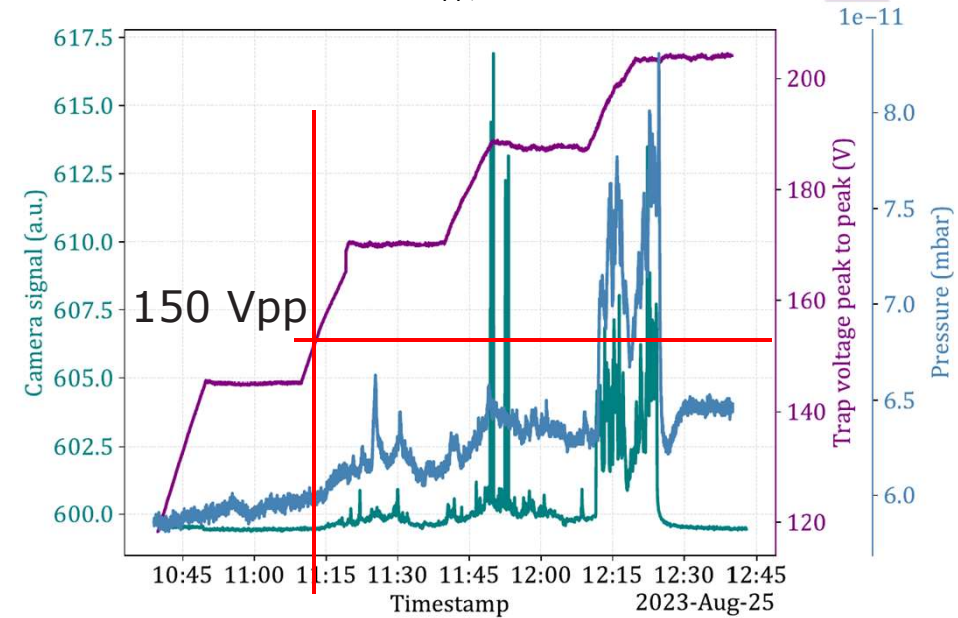
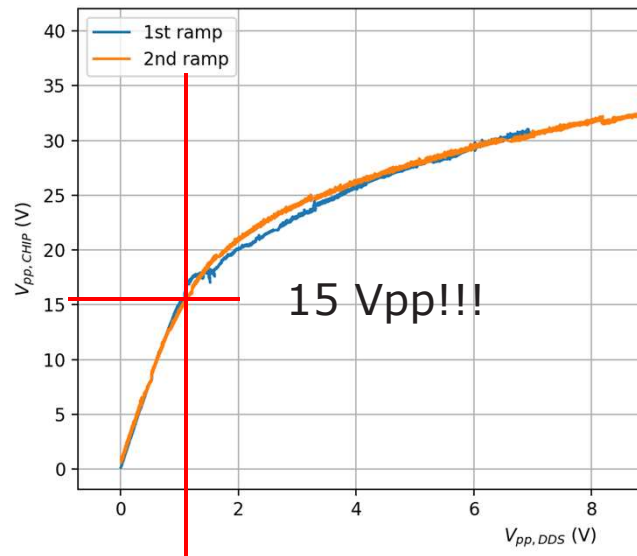
- UHV
- RF supply
- Optical access



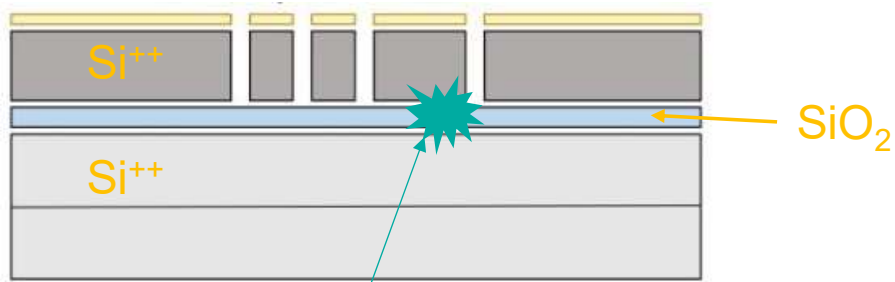
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MICRO-FABRICATED TRAP: BREAKDOWN ORIGIN



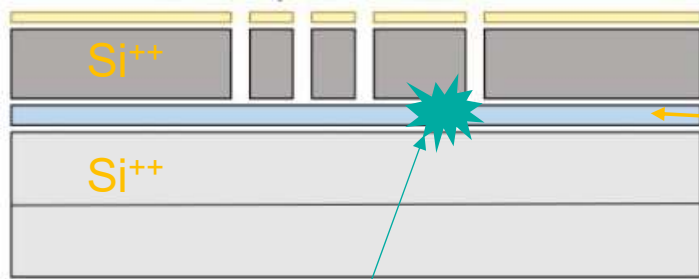
Most likely breakdown point;
matches observations.

BUT: 5 μm of SiO_2 should handle at
least 200-300 V.

TSP tests reveal non-linear
behavior of random electrodes
(junction-like)



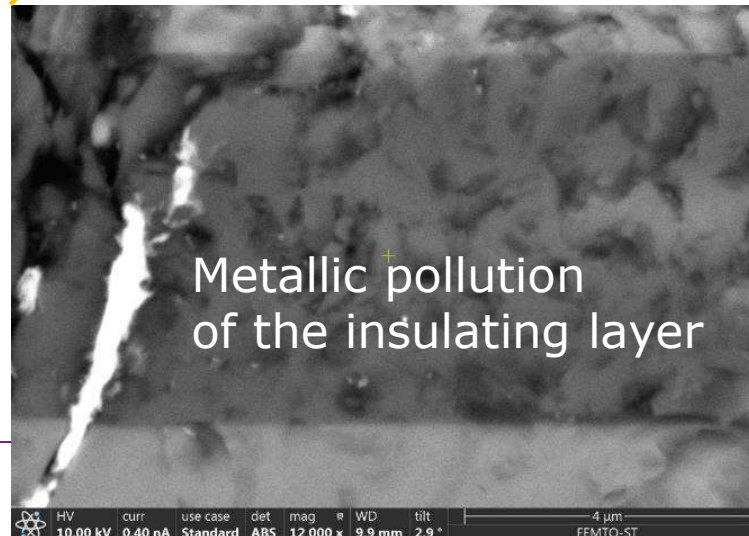
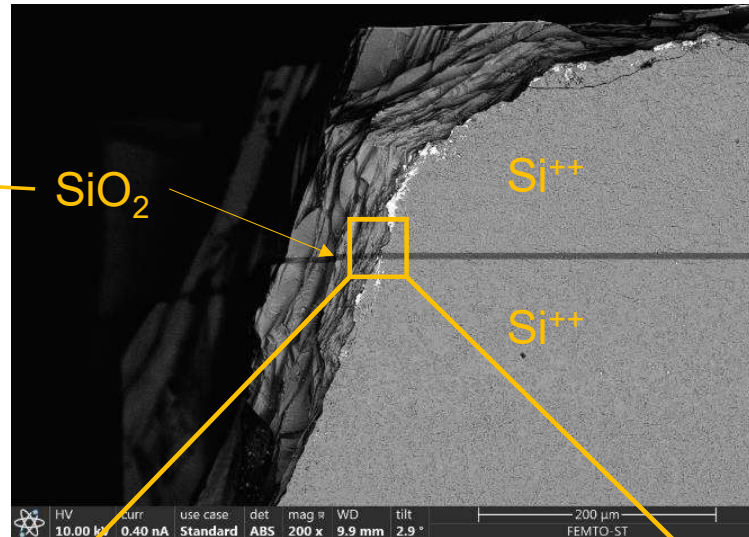
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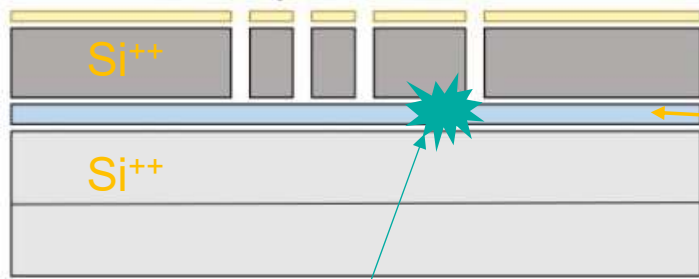
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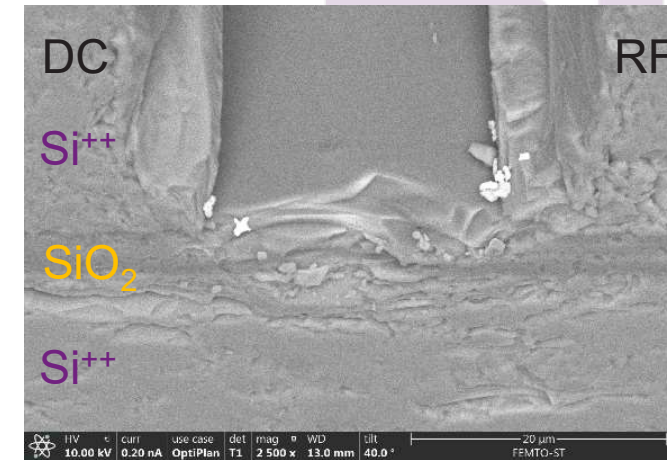
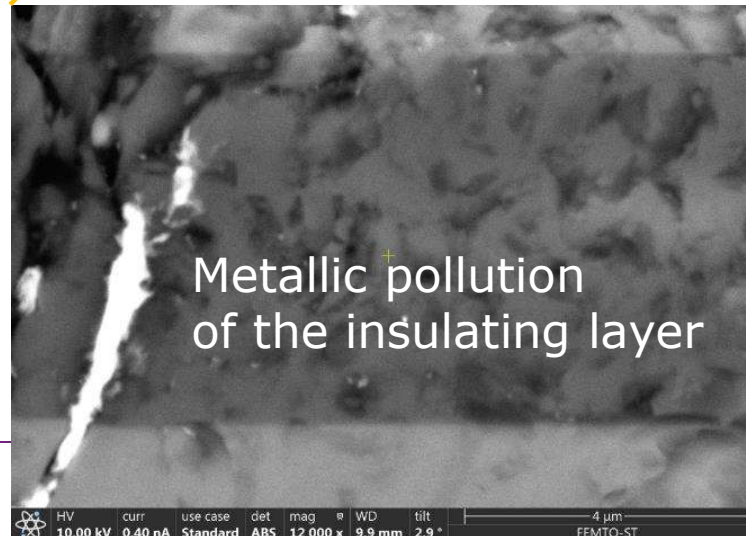
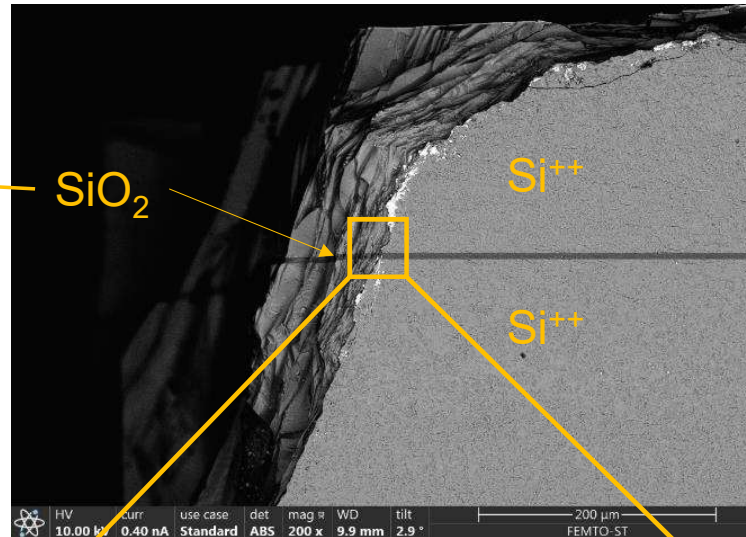
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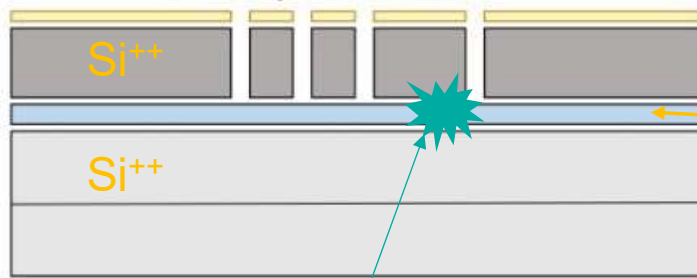
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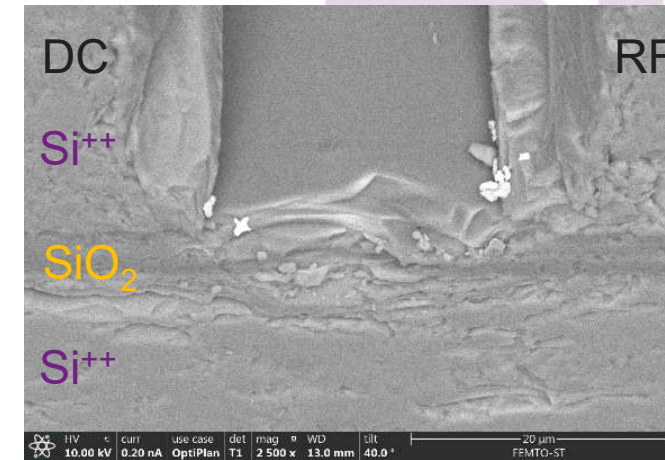
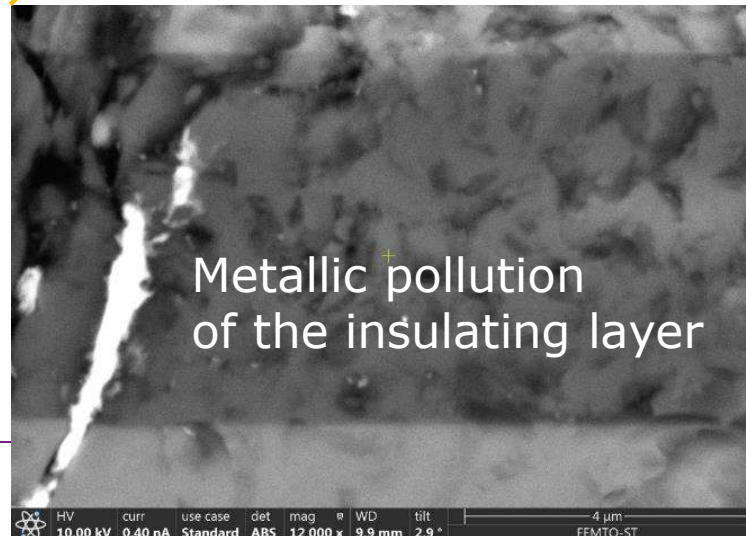
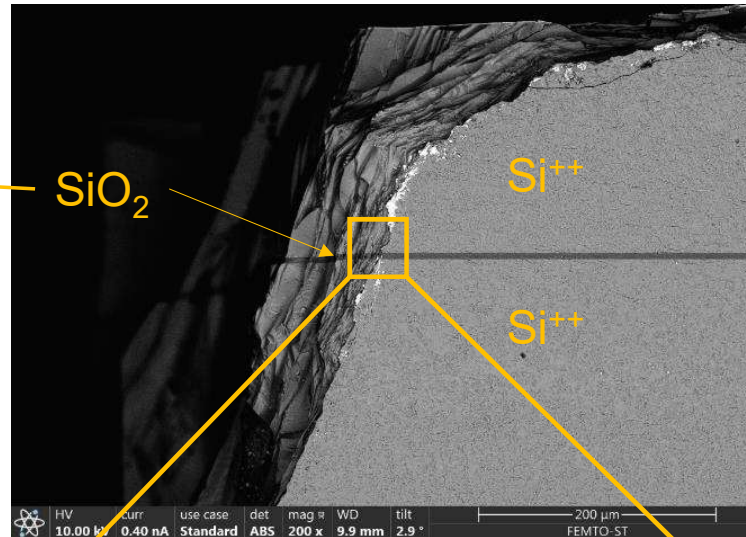
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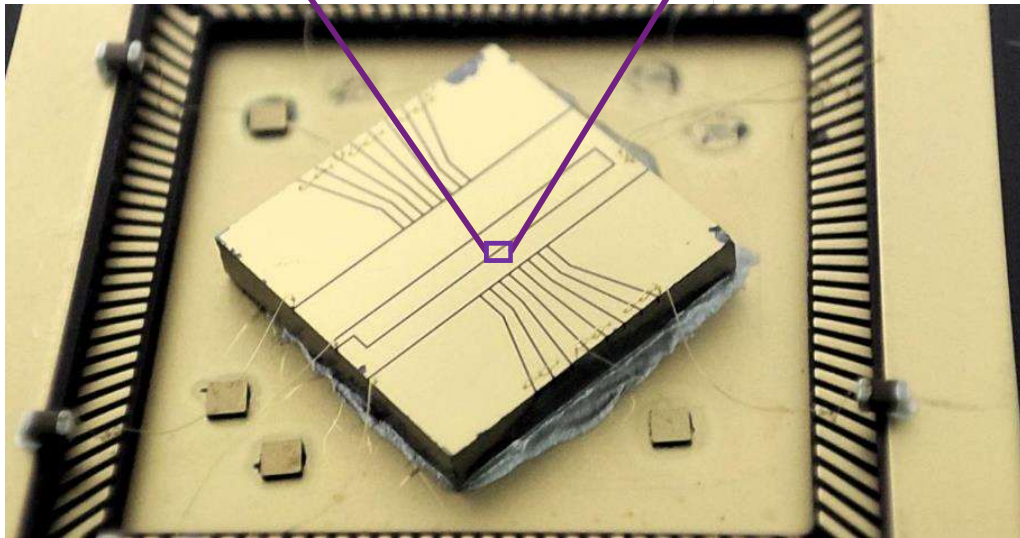
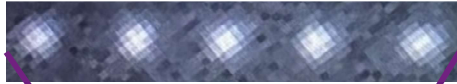


Random behavior due to
random contamination of the
chip flanks.

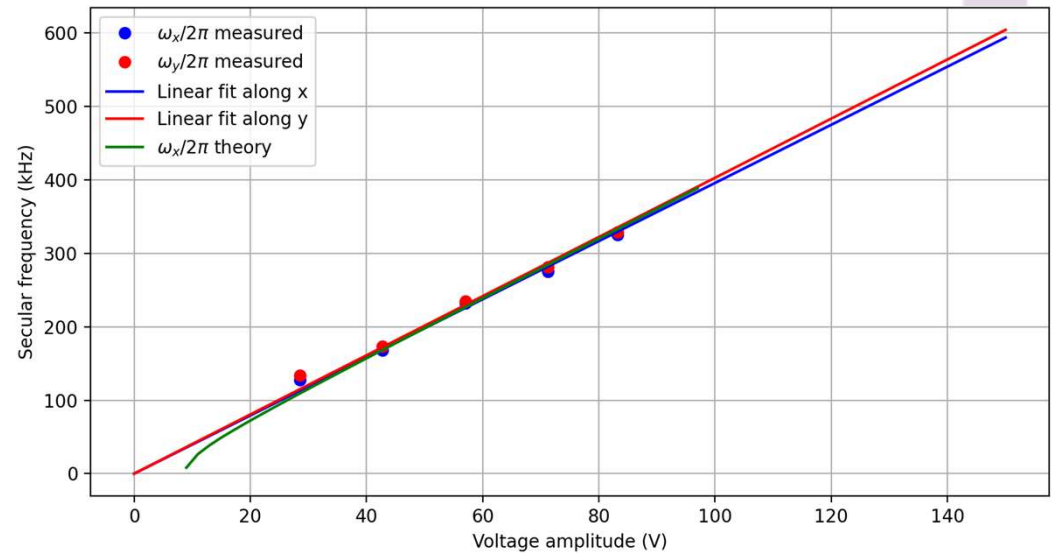
Metallic pollution came from
wafer dicing!

- ⇒ **Easy fix; chip v2 underway**
- ⇒ **Possible to find non-polluted chips.**

MICROFABRICATED TRAP: Sr^+ (PARIS) IONS

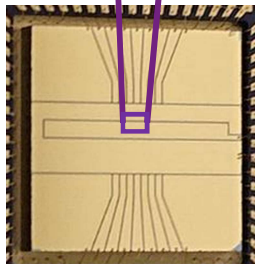
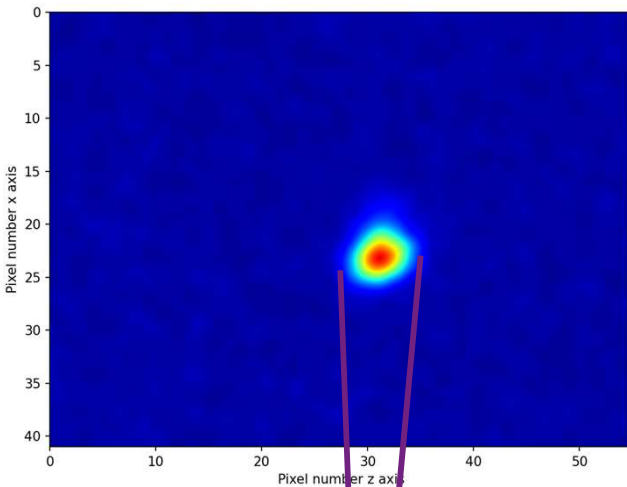


$^{88}\text{Sr}^+$ ions trapping at MPQ
w/ L. Guidoni & J.P. Likforman
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Secular frequencies evolution in the radial plane (x,y)
as a function of the RF voltage
@ $\Omega_{\text{RF}}=4,62$ MHz

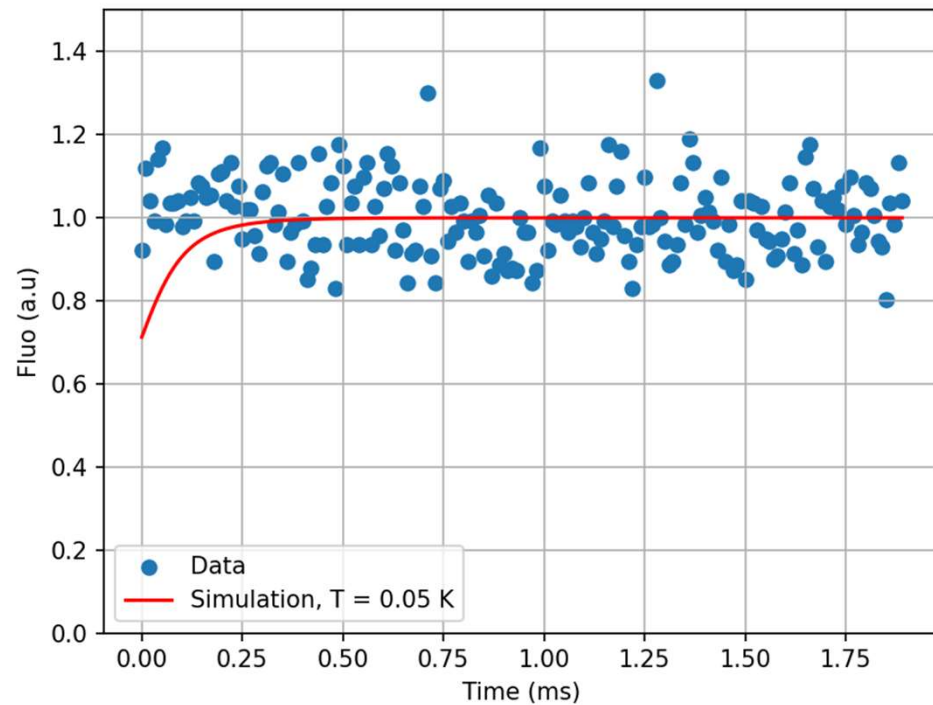
MICROFABRICATED TRAP: YB⁺ (BESANÇON) IONS



- Applied voltages:
 - RF frequency : 3,77 MHz
 - RF voltage : 200 Vpp
 - DC voltages : Between ± 10 V
- Trap:
 - Trap frequencies 80 kHz, 209 kHz and 223 kHz
 - Lifetime 6000 s without clear-out laser, many hours with clear-out laser
 - **Measurement runs > 12 hours regularly**
- Vacuum:
 - Measured 7×10^{-11} mbars
 - Estimated collision rate 8/hour

MICROFABRICATED TRAP: YB⁺ (BESANÇON) IONS

- Heating rate:



Heating rate estimation based on the analysis of the temporal dynamics of a several Doppler cooling cycle [1].

Upper bound estimated **< 1000 phonons/s.**

Heating rate improved by a **factor 10.**

[1] Wesenberg, J. H., et al. "Fluorescence during Doppler cooling of a single trapped atom." *Physical Review A—Atomic, Molecular, and Optical Physics* 76.5 (2007): 053416.

CONCLUSION

- Succesfull design and fabrication of a Surface-electrode for TF metrology.
- Improvement of trap lifetime and heating rate.
- Clock laser installed, clock transition spectroscopy asap.
- 2.0 chip in fabrication, with improved process.
- Should enable higher operating voltages.
- Collaboration with MPQ on trap design, perspective of optical waveguides integration.



ION TRAPPING TEAM

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